

RECTIFIER CHIPS

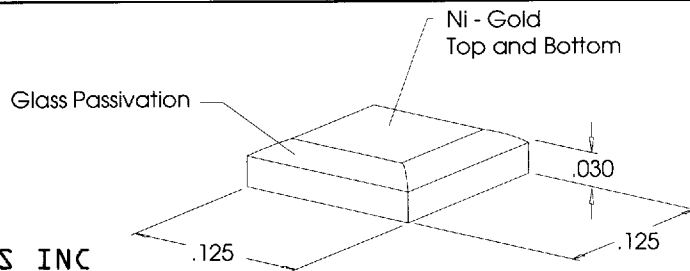
3,000nS RECOVERY

D125S4 D125S8
D125S6 D125S10

$V_{RWM} = 400-1000V$

$T_{RR} = 3,000nS$

Hermetically Sealed



VOLTAGE MULTIPLIERS INC

VMI P/N	Peak Inverse Voltage	Reverse Recovery Time	Forward Voltage Drop		Reverse Leakage Current		Thermal Impedance	Surge Current
	PIV	Trr(6)	VF(1) @ 3.0A	VF(1) @ 9.0A	IR(2) 25°C	IR(2) 100°C	ΘJ-MS(3)	IFS(4)
D125S4	400V(5)	3,000nS	1.0V	1.3V	1.0μA	50μA	0.375°C/W	125A
D125S6	600V(5)	3,000nS	1.0V	1.3V	1.0μA	50μA	0.375°C/W	125A
D125S8	800V(5)	3,000nS	1.2V	1.5V	1.0μA	50μA	0.375°C/W	125A
D125S10	1000V(5)	3,000nS	1.2V	1.5V	1.0μA	50μA	0.375°C/W	125A

(1) Forward Voltage Drop is highly dependent on test contact resistance. Special equipment is required to duplicate measurements.

(2) Reverse Current may require measurement in a suitable dielectric (i.e. fluorinert) to prevent arcing between top and bottom metallized surfaces. Measurement may also require shielding from light.

(3) Thermal Impedance measured from junction to metallized diode surface. Thermal Impedance of mounted device is highly dependent on mounting method and materials. Forward Current rating requires accurate determination of package thermal impedance (silicon die + package thermal impedance). Poorly mounted packages may exceed 100°C/watt while die mounted on large heat sinks may be less than 3°C/watt.

(4) Surge Current testing requires mounting the device in a completed package.

(5) Dielectric coating recommended to eliminate external arcing between metallized surfaces. Minimum distance from top metallization to bottom metallization = .020".

(6) Reverse Recovery Time test conditions: IF= 0.5A, IR= 1.0A, IRR= 0.25A.

(7) Chip Mounting and Bonding: Consult factory for recommendations and requirements.

Dimensions: In • All temperatures are ambient unless otherwise noted. • Data subject to change without notice.



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